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November 1999

# FDS6890A Dual N-Channel 2.5V Specified PowerTrench<sup>™</sup> MOSFET

## **General Description**

These N-Channel 2.5V specified MOSFETs are produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize the on-state resistance and yet maintain low gate charge for superior switching performance.

## Applications

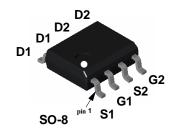
- DC/DC converter
- Motor drives

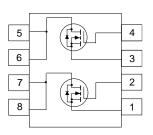
# Features

• 7.5 A, 20 V.  $\rm R_{\rm DS(ON)}$  = 0.018  $\Omega~$  @  $\rm V_{\rm GS}$  = 4.5 V

 $R_{DS(ON)} = 0.022 \ \Omega \ @ V_{GS} = 2.5 \ V.$ 

- Low gate charge (23nC typical).
- Fast switching speed.
- High performance trench technology for extremely low R<sub>DS(ON)</sub>.
- High power and current handling capability.





# Absolute Maximum Ratings TA=25°C unless otherwise noted

Symbol	Parameter		Ratings	Units	
VDSS	Drain-Source Voltage		20	V	
V <sub>GSS</sub>	Gate-Source Voltage		±8	V	
ID	Drain Current - Continuous	(Note 1a)	7.5	A	
	- Pulsed		20		
PD	Power Dissipation for Dual Operation		2.0	W	
	Power Dissipation for Single Operation	(Note 1a)	1.6		
		(Note 1b)	1.0		
		(Note 1c)	0.9		
TJ, T <sub>stq</sub>	Operating and Storage Junction Temperature Range		-55 to +150	°C	

R <sub>e</sub> JA	Thermal Resistance, Junction-to-Ambient	(Note 1a)	78	°C/W
R <sub><sub>θ</sub>JC</sub>	Thermal Resistance, Junction-to-Case	(Note 1)	40	°C/W
			90	

# **Package Marking and Ordering Information**

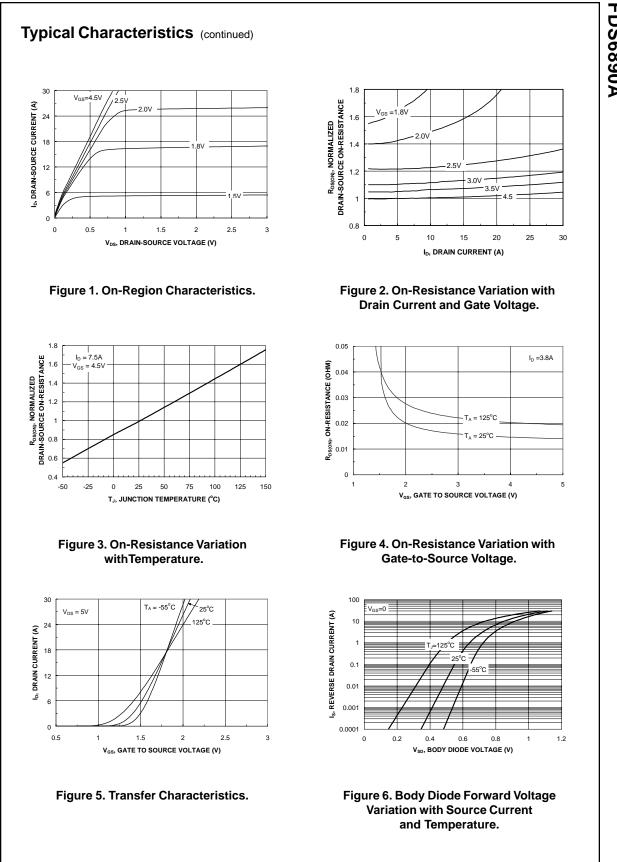
Device Marking	Device	Reel Size	Tape Width	Quantity
FDS6890A	FDS6890A	13	12mm	2500 units

Parameter	Test Conditions	Min	Тур	Max	Units
acteristics					
Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, \text{ I}_{D} = 250 \mu\text{A}$	20			V
Breakdown Voltage Temperature Coefficient	$I_D = 250 \ \mu\text{A}$ , Referenced to $25^{\circ}\text{C}$		14		mV/°C
Zero Gate Voltage Drain Current	$V_{DS} = 16 \text{ V}, V_{GS} = 0 \text{ V}$			1	μA
Gate-Body Leakage Current, Forward				100	nA
Gate-Body Leakage Current, Reverse	$V_{GS} = -8 \text{ V},  V_{DS} = 0 \text{ V}$			-100	nA
acteristics (Note 2)					
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$	0.5	0.8	1.5	V
Gate Threshold Voltage Temperature Coefficient	$I_D = 250 \ \mu\text{A}$ , Referenced to $25^{\circ}\text{C}$		-3.5		mV/°C
Static Drain-Source On-Resistance			0.013 0.021 0.016	0.018 0.034 0.022	Ω
On-State Drain Current	$V_{GS}$ = 10 V, $V_{DS}$ = 5 V	20			А
Forward Transconductance	$V_{DS} = 5 V, I_D = 7.5 A$		35		S
Characteristics					
Input Capacitance	$V_{DS} = 10 V, V_{GS} = 0 V,$		2130		pF
Output Capacitance	☐ f = 1.0 MHz		545		pF
Reverse Transfer Capacitance			270		pF
a Characteristics (New 2)					
	$V_{DD} = 10 V, I_D = 1 A,$		13	24	ns
Turn-On Rise Time	$V_{GS}$ = 4.5 V, $R_{GEN}$ = 6 $\Omega$		26	42	ns
Turn-Off Delay Time	1		65	90	ns
Turn-Off Fall Time	1		23	37	ns
Total Gate Charge	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 7.5 A,		23	32	nC
Gate-Source Charge	$V_{GS} = 4.5 V,$		3.2		nC
Gate-Drain Charge			4.4		nC
urce Diode Characteristics	and Maximum Ratings				
Maximum Continuous Drain-Source				1.3	A
Drain-Source Diode Forward	$V_{GS} = 0 V, I_S = 1.3 A$ (Note 2)		0.65	1.2	V
	Breakdown Voltage Temperature Coefficient Zero Gate Voltage Drain Current Gate-Body Leakage Current, Forward Gate-Body Leakage Current, Reverse Cteristics (Note 2) Gate Threshold Voltage Gate Threshold Voltage Gate Threshold Voltage Temperature Coefficient Static Drain-Source On-Resistance On-State Drain Current Forward Transconductance Characteristics Input Capacitance Output Capacitance Reverse Transfer Capacitance <b>Characteristics</b> (Note 2) Turn-On Delay Time Turn-On Rise Time Turn-Off Fall Time Turn-Off Fall Time Total Gate Charge Gate-Drain Charge Unce Diode Characteristics	Breakdown Voltage Temperature CoefficientIp $250 \ \mu$ A, Referenced to $25^{\circ}$ CIp $250 \ \mu$ A, Referenced to $25^{\circ}$ CIp $250 \ \mu$ A, Referenced to $25^{\circ}$ CGate-Body Leakage Current, Forward $V_{GS} = 16 \ V, V_{GS} = 0 \ V$ Gate-Body Leakage Current, Reverse $V_{GS} = 8 \ V, V_{DS} = 0 \ V$ Gate-Body Leakage Current, Reverse $V_{GS} = -8 \ V, V_{DS} = 0 \ V$ Gate-Body Leakage Current, Reverse $V_{GS} = -8 \ V, V_{DS} = 0 \ V$ Gate-Body Leakage Current, Reverse $V_{GS} = -8 \ V, V_{DS} = 0 \ V$ Gate Threshold Voltage Gate Threshold Voltage $V_{DS} = V_{GS}, \ I_D = 250 \ \mu$ AGate Threshold Voltage Temperature Coefficient $V_{DS} = 10 \ V, \ V_{DS} = 50 \ V_{GS} = 4.5 \ V, \ I_D = 7.5 \ A$ Static Drain-Source On-State Drain Current $V_{DS} = 10 \ V, \ V_{DS} = 5 \ V$ Forward Transconductance $V_{DS} = 10 \ V, \ V_{GS} = 0 \ V, \ f = 1.0 \ MHz$ Input Capacitance Output Capacitance $V_{DS} = 10 \ V, \ I_D = 1 \ A, \ V_{GS} = 4.5 \ V, \ R_{GEN} = 6 \ \Omega$ Turn-On Delay Time Turn-On Rise Time $V_{DS} = 10 \ V, \ I_D = 7.5 \ A, \ V_{GS} = 4.5 \ V, \ R_{GEN} = 6 \ \Omega$ Turn-Off Fall Time $V_{DS} = 10 \ V, \ I_D = 7.5 \ A, \ V_{GS} = 4.5 \ V, \ Gas = 4.5 \ V, \ Gas = 4.5 \ V, \ R_{GS} = 4.$	Breakdown Voltage Temperature CoefficientID $250 \ \mu$ A, Referenced to $25^{\circ}$ CID= $250 \ \mu$ A, Referenced to $25^{\circ}$ CIDZero Gate Voltage Drain Current ForwardVDS= $16 \ V, V_{GS} = 0 \ V$ Gate-Body Leakage Current, ForwardVGS= $8 \ V, V_{DS} = 0 \ V$ Gate-Body Leakage Current, ReverseVGS= $8 \ V, V_{DS} = 0 \ V$ Cteristics (Note 2)(Note 2)ID= $250 \ \mu$ A0.5Gate Threshold Voltage Temperature CoefficientID= $250 \ \mu$ A, Referenced to $25^{\circ}$ CIDStatic Drain-Source On-ResistanceVGS= $4.5 \ V, \ ID = 7.5 \ A, \ TJ = 125^{\circ}$ CVGSOn-State Drain CurrentVGS= $4.5 \ V, \ ID = 7.5 \ A, \ TJ = 125^{\circ}$ C20Forward TransconductanceVDS= $5 \ V, \ ID = 7.5 \ A$ 20Forward TransconductanceVDS= $5 \ V, \ ID = 7.5 \ A$ 20Forward TransconductanceVDS= $10 \ V, \ V_{GS} = 0 \ V, \ f = 1.0 \ MHz$ IDInput Capacitance Reverse Transfer CapacitanceVDD= $10 \ V, \ ID = 1 \ A, \ V_{GS} = 4.5 \ V, \ R_{GEN} = 6 \ \Omega$ IDTurn-On Blay Time Turn-Off Delay TimeVDS= $10 \ V, \ ID = 7.5 \ A, \ V_{GS} = 4.5 \ V, \ R_{GS} = 4.5 \ V, \ R_{GS$	Breakdown Voltage Temperature CoefficientIb $250 \ \mu$ A, Referenced to $25^{\circ}$ C14Ib $250 \ \mu$ A, Referenced to $25^{\circ}$ C14Zero Gate Voltage Drain Current Forward $V_{DS} = 16 \ V, V_{GS} = 0 \ V$ 14Gate-Body Leakage Current, Forward $V_{GS} = 8 \ V, V_{DS} = 0 \ V$ 14Gate-Body Leakage Current, Reverse $V_{GS} = 8 \ V, V_{DS} = 0 \ V$ 14Gate-Body Leakage Current, Reverse $V_{GS} = -8 \ V, V_{DS} = 0 \ V$ 14Gate-Body Leakage Current, Reverse $V_{GS} = -8 \ V, V_{DS} = 0 \ V$ 16Gate-Threshold Voltage Coefficient $V_{DS} = V_{GS}, I_D = 250 \ \mu$ A0.50.8Gate Threshold Voltage Temperature Coefficient $I_D = 250 \ \mu$ A, Referenced to $25^{\circ}$ C-3.5Static Drain-Source On-State Drain Current $V_{GS} = 4.5 \ V, I_D = 7.5 \ A, T_J = 125^{\circ}$ C $V_{GS} = 2.5 \ V, I_D = 6.5 \ A$ 0.013 $0.021 \ V_{GS} = 2.5 \ V, I_D = 6.5 \ A$ 0.013 $0.021 \ V_{GS} = 10 \ V, V_{DS} = 5 \ V$ 20Forward Transconductance $V_{DS} = 5 \ V, I_D = 7.5 \ A$ 3535Characteristics Input Capacitance Reverse Transfer Capacitance Turn-On Delay Time $V_{DS} = 10 \ V, I_D = 1 \ A, V_{CS} = 4.5 \ V, R_{GEN} = 6 \ \Omega$ 26Turn-Off Fall Time Turn-Off Fall Time $V_{DS} = 10 \ V, I_D = 7.5 \ A, V_{CS} = 4.5 \ V, GS = 4.5 \$	Breakdown Voltage Temperature CoefficientIb b $250 \mu$ A, Referenced to $25^{\circ}$ C14Zero Gate Voltage Drain Current Gate-Body Leakage Current, Forward $V_{DS} = 16 V, V_{GS} = 0 V$ 1Gate-Body Leakage Current, Reverse $V_{GS} = 8 V, V_{DS} = 0 V$ 100Gate-Body Leakage Current, Reverse $V_{GS} = -8 V, V_{DS} = 0 V$ -100Gate Threshold Voltage Static Drain-Source $V_{DS} = V_{GS}, I_D = 250 \mu$ A0.50.81.5Gate Threshold Voltage On-Resistance $V_{DS} = V_{GS}, I_D = 250 \mu$ A0.50.81.5On-Resistance $V_{GS} = 4.5 V, I_D = 7.5 A$ 0.0130.0180.0210.034On-State Drain Current $V_{GS} = 4.5 V, I_D = 7.5 A$ 0.0160.0220.0160.022On-State Drain Current $V_{GS} = 10 V, V_{DS} = 5 V$ 2020202020Forward Transconductance $V_{DS} = 10 V, V_{GS} = 0 V,$ 2130110.160.022Output Capacitance Reverse Transfer Capacitance $V_{DD} = 10 V, I_D = 1 A,$ $V_{GS} = 4.5 V, R_{GEN} = 6 \Omega$ 22642Turm-On Delay Time Turm-On Rise Time $V_{DS} = 10 V, I_D = 7.5 A,$ $V_{GS} = 4.5 V,$ 2337Total Gate Charge Gate-Source Charge $V_{DS} = 10 V, I_D = 7.5 A,$ $V_{GS} = 4.5 V,$ 2332Gate-Source Charge Gate-Source Charge $V_{DS} = 10 V, I_D = 7.5 A,$ $V_{GS} = 4.5 V,$ 2332Turm-Of feall Time Gate-Source Charge $V_{DS} = 10 V, I_D = 7.5 A,$ $V_{GS} = 4.5 V,$ 3.232Gate-Drain Charge </td

Scale 1 : 1 on letter size paper

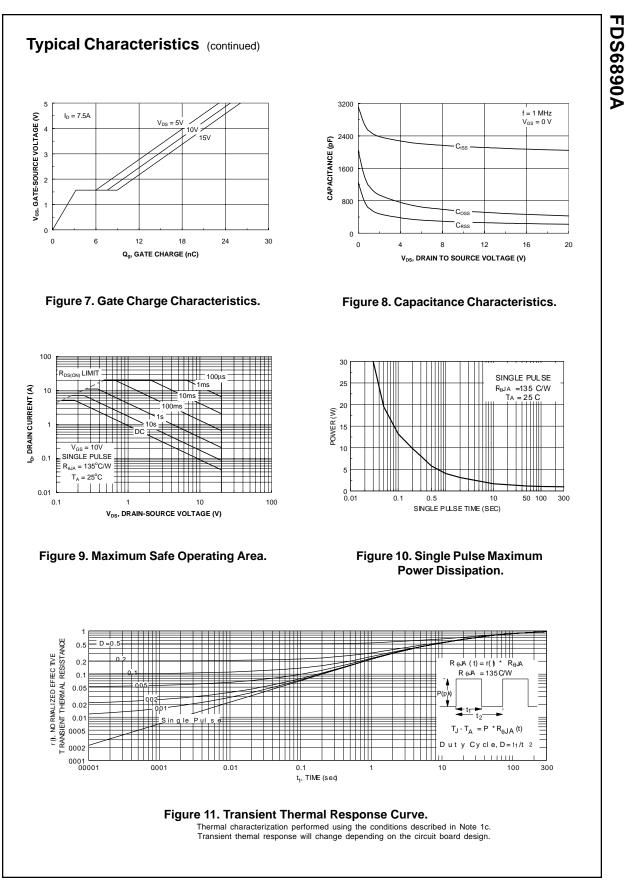
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